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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number	~~Unknown~~ 10/789203
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	~~Unknown~~ 2815
Examiner Name	~~Unknown~~ Ecker

Sheet 1 of 11

Attorney Docket No: 303.356US4

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	Group Art Unit	~~Unknown~~ 2815
	Examiner Name	~~Unknown~~ Eckert
Sheet 2 of 11	Attorney Docket No: 303.356US4	

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Group Art Unit	~~Unknown~~ 2815
Examiner Name	~~Unknown~~ ECKERT

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EXAMINER JSC Eckert DATE CONSIDERED 1/31/05

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	First Named Inventor	Forbes, Leonard
	Group Art Unit	~~Unknown~~ 2815
	Examiner Name	~~Unknown~~ Eckert
Sheet 4 of 11	Attorney Docket No: 303.356US4	

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Sheet 5 of 11

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Group Art Unit	~~Unknown~~ 2815
Examiner Name	~~Unknown~~ ECKERT

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Application Number	~~Unknown~~ 10/789203
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	~~Unknown~~ 2815
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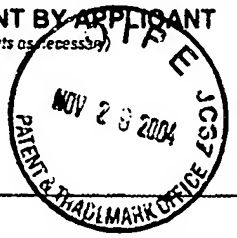

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Sheet 1 of 1

Attorney Docket No: 303.356US4

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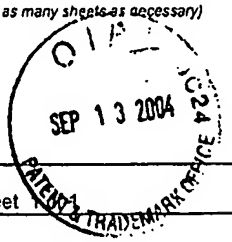

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